onsemi

MOSFET – Single, N-Channel, Small Signal, SC-88

25 V, 1.2 A

NTJS4405N, NVJS4405N

Features

- Advance Planar Technology for Fast Switching, Low RDS(on)
- Higher Efficiency Extending Battery Life
- AEC-Q101 Qualified and PPAP Capable NVJS4405N
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Boost and Buck Converter
- Load Switch
- Battery Protection

MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

Symbol	Rating	9		Value	Unit
V _{DSS}	Drain-to-Source Voltage		25	V	
V _{GS}	Gate-to-Source Voltage			± 8.0	V
I _D	Drain Current	t < 5 s	$T_A = 25^{\circ}C$	1.2	А
I _D	Continuous Drain Current	Steady	$T_A = 25^{\circ}C$	1.0	А
	(Note 1)	State	$T_A = 75^{\circ}C$	0.80	
PD	Power Dissipation (Note 1)	Stead	dy State	0.63	W
PD	Power Dissipation (Note 1)	t≤	≤ 5 s	0.89	W
I _{DM}	Pulsed Drain Current	t _p =	10 μs	3.7	А
T _J , T _{STG}	Operating Junction and Storage Temperature				°C
۱ _S	Source Current (Body Dioc	0.8	А		
TL	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			260	°C
	ESD Rating – Machine Mo	del		25	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Symbol	Rating	Мах	Unit
$R_{\theta JL}$	Junction-to-Lead - Steady State (Note 1)	102	°C/W
$R_{\theta JA}$	Junction-to-Ambient - Steady State (Note 1)	200	
$R_{\theta JA}$	Junction-to-Ambient – t \leq 5 s (Note 1)	140	

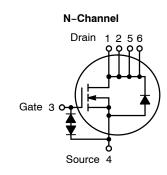
1. Surface mounted on FR4 board using 1 in sq pad size

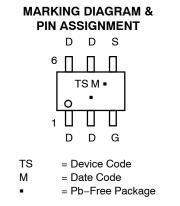
(Cu area = 1.127 in sq [1 oz] including traces).

V _{(BR)DSS}	R _{DS(on)} Typ	I _D Max
25 V	249 mΩ @ 4.5 V	1.2 A
	299 m Ω @ 2.7 V	1.2 A



SC-88/SOT-363 CASE 419B





(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NTJS4405NT1G	SC-88 (Pb-Free)	3,000 / Tape & Reel
NVJS4405NT1G	SC-88 (Pb-Free)	3,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, <u>BRD8011/D</u>.

NTJS4405N, NVJS4405N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Characteristic	Test Condition		Min	Тур	Max	Unit
OFF CHARAG	OFF CHARACTERISTICS						
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	V_{GS} = 0 V, I _D = 250 μ A		25			V
V _{(BR)DSS} /T _J	Drain-to-Source Breakdown Voltage Temperature Coefficient				30		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0 V, V _{DS} = 20 V	$T_J = 25^{\circ}C$			1.0	μΑ
		V _{DS} = 20 V	T _J = 125°C			10	
I _{GSS}	Gate-to-Source Leakage Current	V _{DS} = 0 V, V _G	_{iS} = 8.0 V			100	nA

ON CHARACTERISTICS (Note 2)

V _{GS(TH)}	Gate Threshold Voltage	V_{GS} = V_{DS} , I_D = 250 μ A	0.65		1.5	V
V _{GS(TH)} /T _J	Negative Threshold Temperature Coefficient			-2.0		mV/°C
R _{DS(on)}	Drain-to-Source On Resistance	V_{GS} = 4.5 V, I _D = 0.6 A		249	350	mΩ
		V_{GS} = 2.7 V, I _D = 0.2 A		299	400	
		V_{GS} = 4.5 V, I _D = 1.2 A		260		
9 FS	Forward Transconductance	$V_{DS} = 5.0 \text{ V}, \text{ I}_{D} = 0.5 \text{ A}$		0.5		S

CHARGES AND CAPACITANCES

C _{ISS}	Input Capacitance		49	60	pF
C _{OSS}	Output Capacitance	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 10 V	22.4	30	
C _{RSS}	Reverse Transfer Capacitance	20	8.0	12	
Q _{G(TOT)}	Total Gate Charge		0.75	1.5	nC
Q _{G(TH)}	Threshold Gate Charge	V _{GS} = 4.5 V, V _{DS} = 5.0 V, I _D = 0.95 A	0.10		
Q _{GS}	Gate-to-Source Charge	I _D = 0.95 A	0.30	0.50	
Q _{GD}	Gate-to-Drain Charge		0.20	0.40	

SWITCHING CHARACTERISTICS (Note 3)

t _{d(ON)}	Turn-On Delay Time	V_{GS} = 4.5 V, V _{DS} = 6.0 V, I _D = 0.5 A, R _G = 50 Ω			6.0	12	ns
t _r	Rise Time				4.7	8.0	
t _{d(OFF)}	Turn-Off Delay Time				25	35	
t _f	Fall Time				41	60	
DRAIN-SOURCE DIODE CHARACTERISTICS							
V _{SD}	Forward Diode Voltage	V _{GS} = 0 V,	T _J = 25°C		0.82	1.20	V

 $I_{\rm S} = 0.6 \, \rm A$

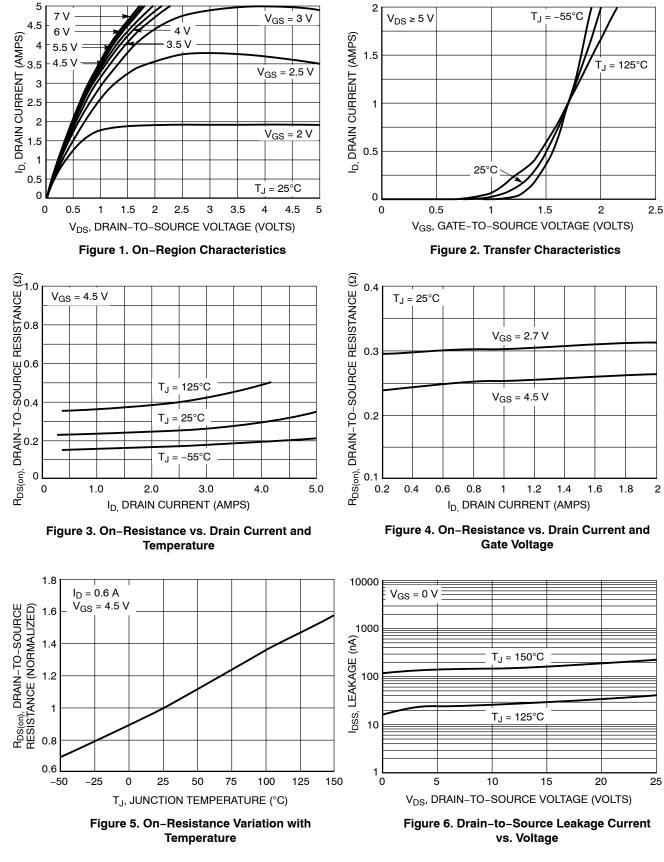
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: pulse width $\leq 300 \ \mu$ s, duty cycle $\leq 2\%$. 3. Switching characteristics are independent of operating junction temperatures.

NTJS4405N, NVJS4405N

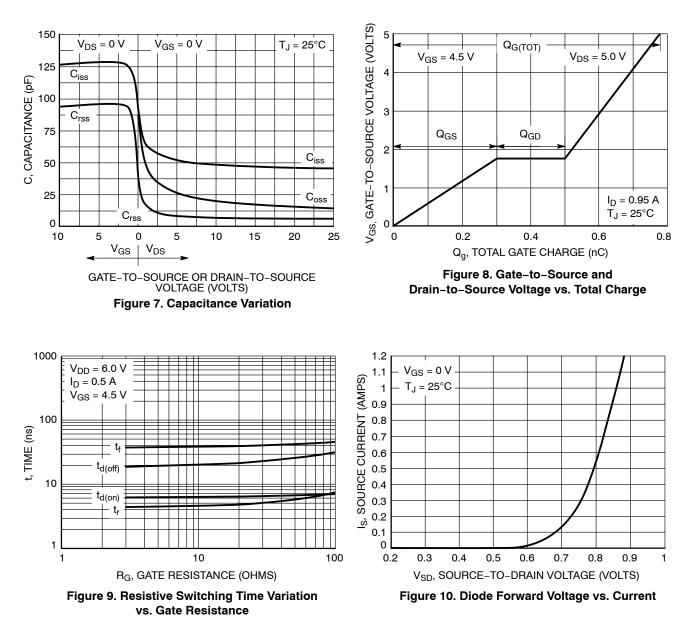
2 7 V $T_J = -55^{\circ}C$ $V_{GS} = 3 V$ $V_{DS} \ge 5 V$ 6 V 4 V 3.5 V 1.5 4.5 V_{GS} = 2.5 V 1

TYPICAL PERFORMANCE CURVES ($T_J = 25^{\circ}C$ UNLESS OTHERWISE NOTED) (continued)



NTJS4405N, NVJS4405N

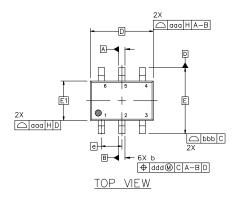
TYPICAL PERFORMANCE CURVES (T_J = 25°C UNLESS OTHERWISE NOTED) (continued)



semi

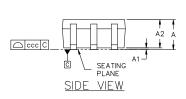
SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

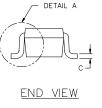
DATE 18 APR 2024

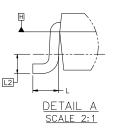




- DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018.
- 2.
- ALL DIMENSION ARE IN MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 3. PER END.
- 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF
- DATUMS A AND B ARE DETERMINED AT DATUM H. 5.
- DIMENSIONS & AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. 7 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION & AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.







	MILLIMETERS					
DIM	MIN.	NOM.	MAX.			
А			1.10			
A1	0.00		0.10			
A2	0.70	0.90	1.00			
b	0.15	0.20	0.25			
с	0.08	0.15	0.22			
D		2.00 BSC				
E		2.10 BSC				
E1		1.25 BSC				
е		0.65 BSC)			
L	0.26	0.36	0.46			
L2	0.15 BSC					
aaa	0.15					
bbb	0.30					
ccc	0.10					
ddd		0.10				

6X 0.66 6X 0.30-2.50 0.65 PITCH

RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

XXX = Specific Device Code Μ

GENERIC **MARKING DIAGRAM***

XXXM.

. 0

6

- = Date Code*
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42985B	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	SC-88 2.00x1.25x0.90, 0.65P		PAGE 1 OF 2			
onsemi and ONSEMi, are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation						

special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

DOCUMENT NUMBER:	98ASB42985B Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	SC-88 2.00x1.25x0.90, 0.65P		PAGE 2 OF 2			

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>